

# CBCS SCHEME

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15EC32

## Third Semester B.E. Degree Examination, Dec.2019/Jan.2020 Analog Electronics

Time: 3 hrs.

Max. Marks: 80

**Note: Answer FIVE full questions, choosing one full question from each module.**

### Module-1

- 1 a. Draw the circuit diagram of common Emitter fixed bias configuration. Derive the expression for  $Z_i$ ,  $Z_o$ ,  $A_v$  using  $r_e$  model. (08 Marks)
- b. For the network shown in Fig. Q1 (b), determine  $Z_i$ ,  $Z_o$ ,  $A_v$  and  $A_i$ . Given  $h_{ie} = 1.175 \text{ K}\Omega$ ,  $h_{fe} = 120$ ,  $h_{oe} = 20 \mu\text{A/v}$  using approximate hybrid equivalent model. (08 Marks)

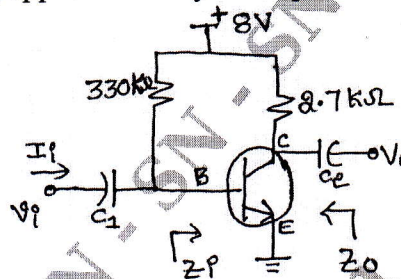


Fig. Q1 (b)

OR

- 2 a. Draw ' $r_e$ ' and 'h'-parameter models for a transistor in common Emitter configuration. Also give relation between ' $r_e$ ' and 'h'-parameter. (05 Marks)
- b. For the circuit shown below, calculate  $r_e$ ,  $Z_i$ ,  $Z_o$  and  $A_v$ , while consider  $r_o = \infty$ . (08 Marks)

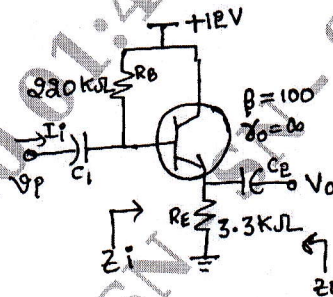


Fig. Q2 (b)

- c. What are the advantages of h-parameters? (03 Marks)

### Module-2

- 3 a. Explain the small signal model of the FET. (04 Marks)
- b. Derive the expression for  $Z_i$ ,  $Z_o$  and  $A_v$  for FET voltage divider bias circuit. (08 Marks)
- c. Compare JFET and MOSFET. (04 Marks)

OR

- 4 a. Explain the n-channel enhancement type MOSFETs, with their characteristics curves. (08 Marks)
- b. Derive the expression for  $Z_i$ ,  $Z_o$  and  $A_v$  for FET self biased configuration (with  $R_s$  bypassed). (08 Marks)

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.  
2. Any revealing of identification, appeal to evaluator and /or equations written eg. 42+8 = 50, will be treated as malpractice.



Module-3

- 5 a. Prove that  
Input capacitance is  $C_{Mi} = (1 - A_v)C_f$  and  
Output capacitance is  $C_{MO} = \left(1 - \frac{1}{A_v}\right)C_f$  using miller effect. (08 Marks)
- b. Describe the factors that affect the low frequency response of a BJT-CE amplifier. (08 Marks)

OR

- 6 a. Explain high frequency response of FET amplifier and derive expression for cut off frequencies, defined by input and output circuits ( $f_{Hi}$  and  $f_{Ho}$ ). (08 Marks)
- b. Determine the lower cut off frequency for the network shown in Fig. Q6 (b), using following parameters  $g_m = 2 \text{ ms}$ ,  $r_d = \infty \Omega$ ,  $I_{DSS} = 8 \text{ mA}$ ,  $V_P = -4 \text{ V}$ ,  $V_{DD} = 20 \text{ V}$ . (08 Marks)

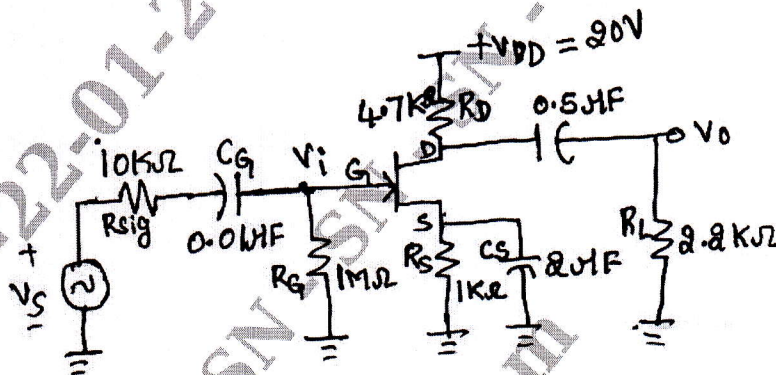


Fig. Q6 (b)

Module-4

- 7 a. With the help of a neat circuit diagram, explain the working of Hartley oscillator. (08 Marks)
- b. The following data for Colpitts oscillator are as follows :  $C_1 = 1 \text{ nF}$ ,  $C_2 = 99 \text{ nF}$ ,  $L = 1.5 \text{ mH}$  and  $h_{fe} = 110$ . Calculate frequency of oscillation for the same. (04 Marks)
- c. Explain the important advantages of a negative feedback amplifier. (04 Marks)

OR

- 8 a. Mention the types of feedback connections. Draw their block diagrams indicating input and output signal. (08 Marks)
- b. Obtain expression for  $Z_{if}$ ,  $Z_{of}$  for a voltage series feedback. (08 Marks)

Module-5

- 9 a. Explain the operation of a class B push-pull amplifier and also show that its efficiency is 78.50%. (08 Marks)
- b. With a neat circuit diagram, explain the operation of a transformer coupled class A power amplifier. (08 Marks)

OR

- 10 a. For a harmonic distortion reading of  $D_2 = 0.1$ ,  $D_3 = 0.02$  and  $D_4 = 0.01$ , with  $I_1 = 4 \text{ A}$  and  $R_C = 8 \Omega$ , calculate the total harmonic distortion, fundamental power and total power. (04 Marks)
- b. What are the classification of power amplifiers, based on the location of Q - point? Discuss them briefly. (08 Marks)
- c. With the help of neat block diagram, explain the working of shunt voltage regulator. (04 Marks)

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